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6115292

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TITLE:

Memory configuration of a composite memory device

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1998

Brief Summary Text - BSTX (21):

According to another aspect of the present invention, a composite flash memory device according to claim 1, further includes a selector selecting an single sector erasing mode which the sectors of the flash memory device are erased by a sector unit and a simultaneously plural sector erasing mode that simultaneously erases the sectors of a regular range in the plural sector flash memory device.

Detailed Description Text - DETX (13):

In this embodiment, the composite flash memory device 100 is capable of erasing the only one sector comprised of 128-byte unit, also erasing one block comprised of 8 K byte unit (64 sectors) and furthermore, erasing certain range of plural 8 K byte unit.

Detailed Description Text - DETX (15):

Now referring to FIG. 4, a selector circuit 39 is located in the composite flash memory device 100 and can select two erasing modes. One mode is a single erasing mode that selected only one sector of the flash memory 12B is erased. The other mode is a block unit erasing mode that the selected single block or

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plural block corresponding to the selected range of the $\underline{\text{flash}}$ memory 12B is $\underline{\text{erased}}$.

Claims Text - CLTX (7):

a selector for selecting a single <u>sector erasing</u> mode in which the <u>sectors</u> of the first <u>flash</u> memory array are <u>erased by a sector unit and a simultaneously plural sector erasing mode that simultaneously erases the <u>sectors</u> of a regular range in the first <u>flash</u> memory array.</u>

Claims Text - CLTX (14):

selector means for selecting a single <u>sector erasing</u> mode in which the <u>sectors</u> of said first <u>flash</u> memory means are <u>erased by a sector unit and a simultaneously plural sector erasing mode that simultaneously erases the <u>sectors</u> of a regular range in the first <u>flash</u> memory means.</u>

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